
Non traditional manufacturing processes (2)

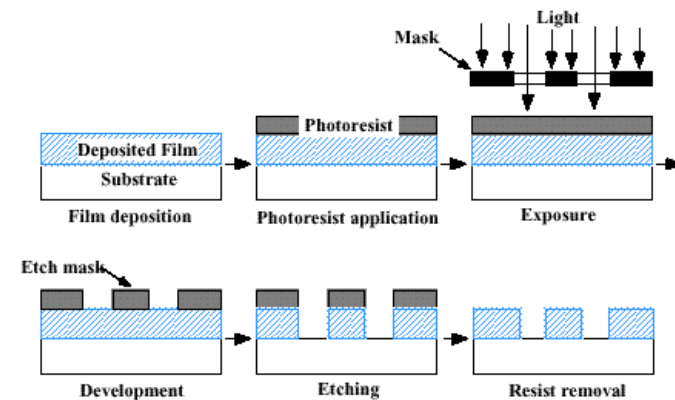
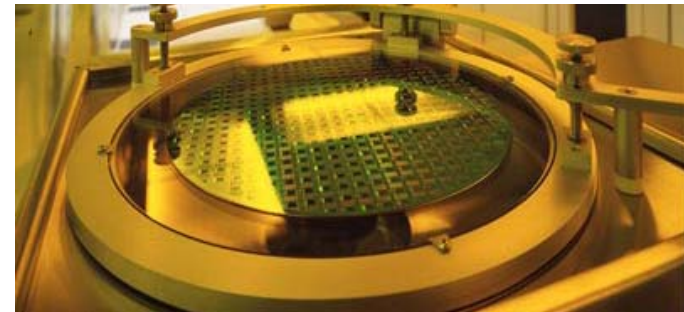
Seok-min Kim
smkim@cau.ac.kr



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Photolithography

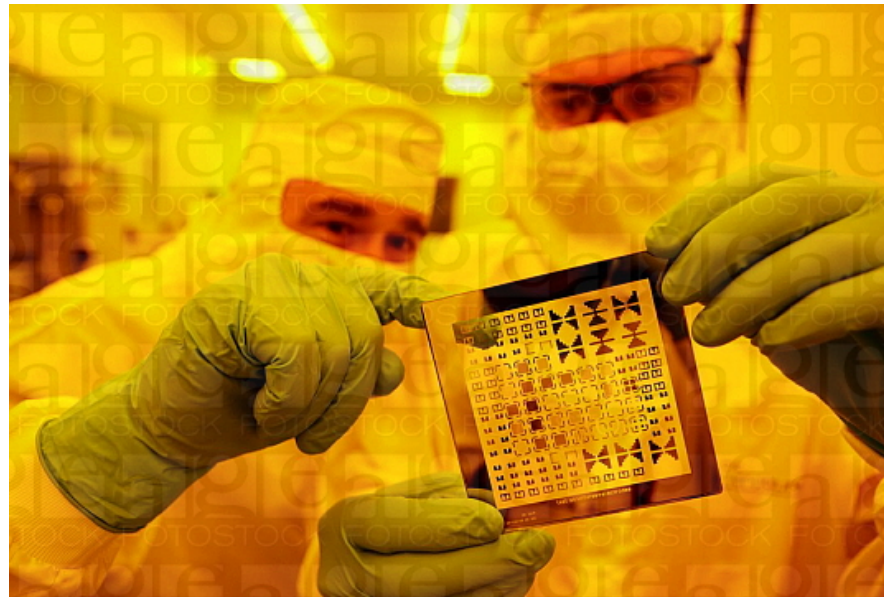
- Uses light radiation to expose a coating of photoresist on the surface of the wafer
 - Common light source in wafer processing is ultraviolet light, due to its short wavelength
- A *mask* containing the required geometric pattern for each layer separates the light source from the wafer, so that only the portions of the photoresist not blocked by the mask are exposed



<http://www.youtube.com/watch?v=aCOyq4YzBtY&feature=related>

Photolithography Mask

- Flat plate of transparent glass onto which a thin film of an opaque substance has been deposited in certain areas to form the desired pattern
- The mask itself is fabricated by lithography, the pattern being based on circuit design data, usually in the form of digital output from the CAD system used by circuit designer



B20-1081690 - (c) - Javier Larrea

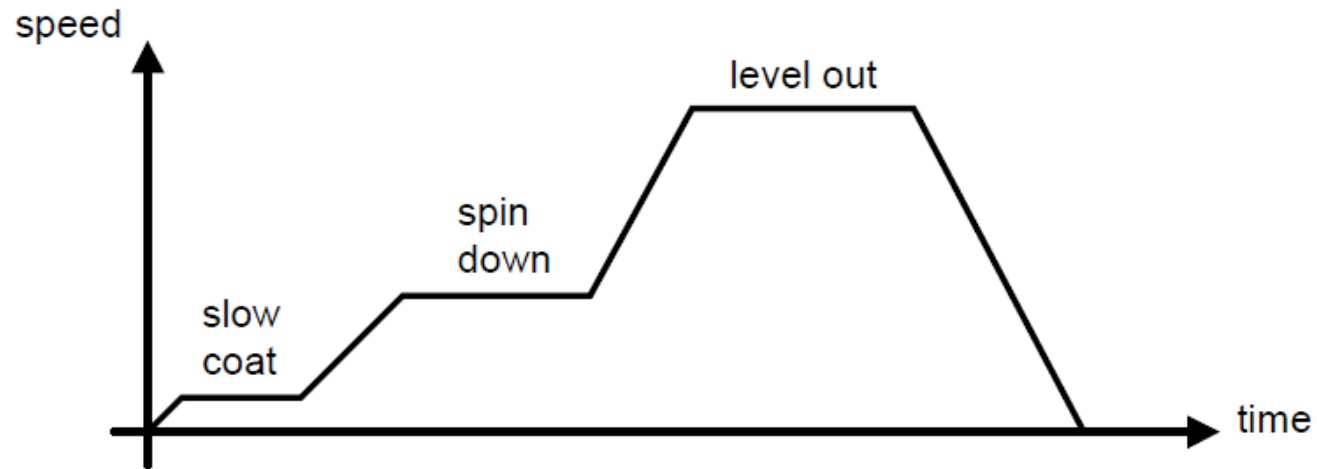
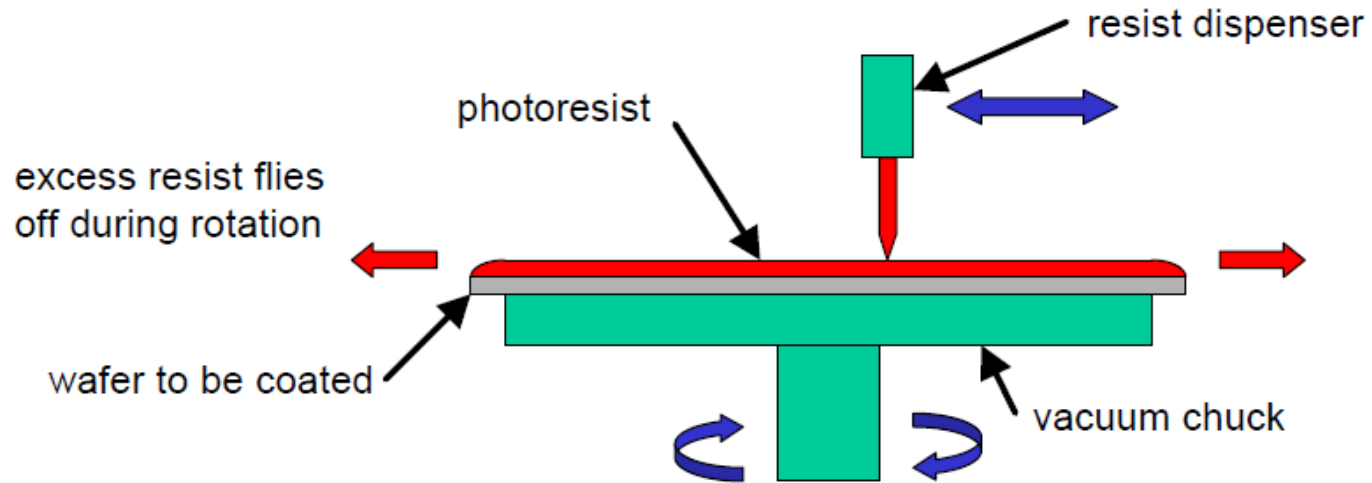
Photoresist

- Organic polymer that is sensitive to light radiation in a certain wavelength range
- Sensitivity causes either increase or decrease in solubility of the polymer to certain chemicals
- Typical practice in semiconductor processing is to use photoresists sensitive to UV light
 - UV light has a short wavelength compared to visible light, permitting sharper imaging of circuit details on wafer surface
- Also permits fabrication areas in plant to be illuminated at low light levels outside UV band

Photoresist Spin Coating

- Wafer is held on a spinner chuck by vacuum and resist is coated to uniform thickness by spin coating.
- Typically 3000-6000 rpm for 15-30 seconds.
- Resist thickness is set by:
 - primarily resist viscosity
 - secondarily spinner rotational speed
- Resist thickness is given by $t = kp^2/w^{1/2}$, where
 - k = spinner constant, typically 80-100
 - p = resist solids content in percent
 - w = spinner rotational speed in rpm/1000
- Most resist thicknesses are 1-2 μm for commercial Si processes

Photoresist Spin Coating



Stages of Resist Coating



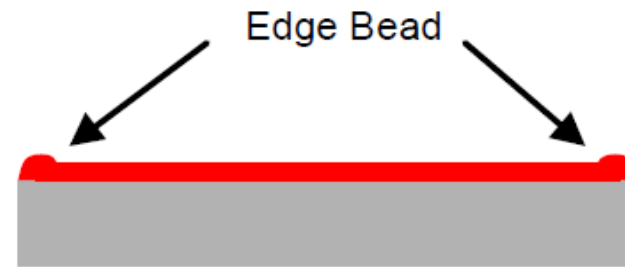
1. EQUILIBRIUM STAGE
(stopped)



2. WAVE-FORMATION STAGE
(~ 2 revolutions)



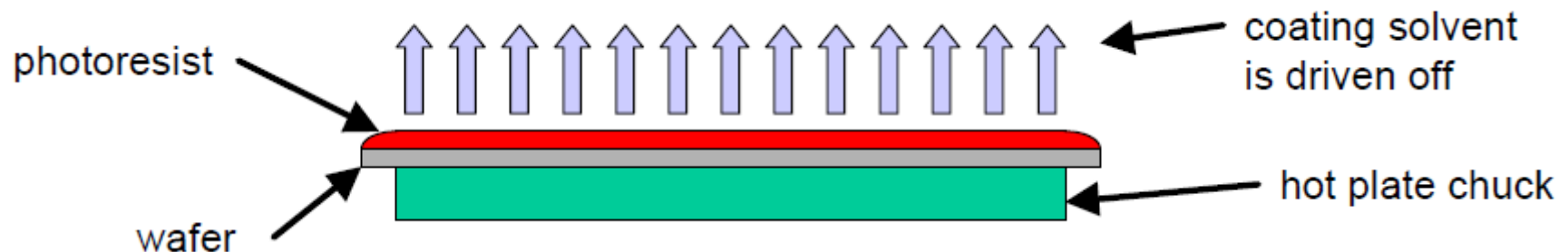
3. CORONA STAGE
(~ 30 revolutions)



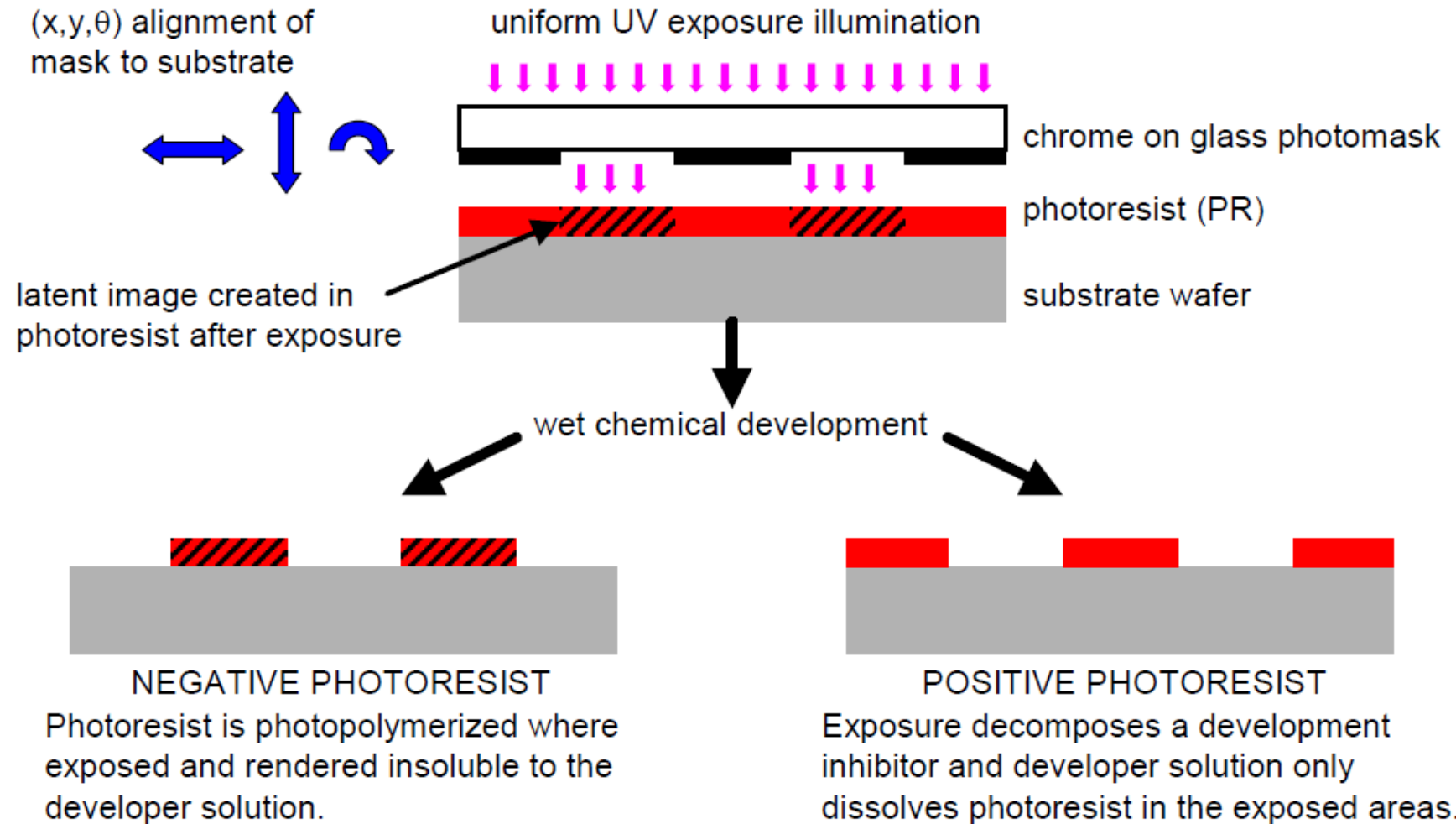
4. SPIRAL STAGE
(~ 1000 revolutions)

Prebake (Soft Bake)

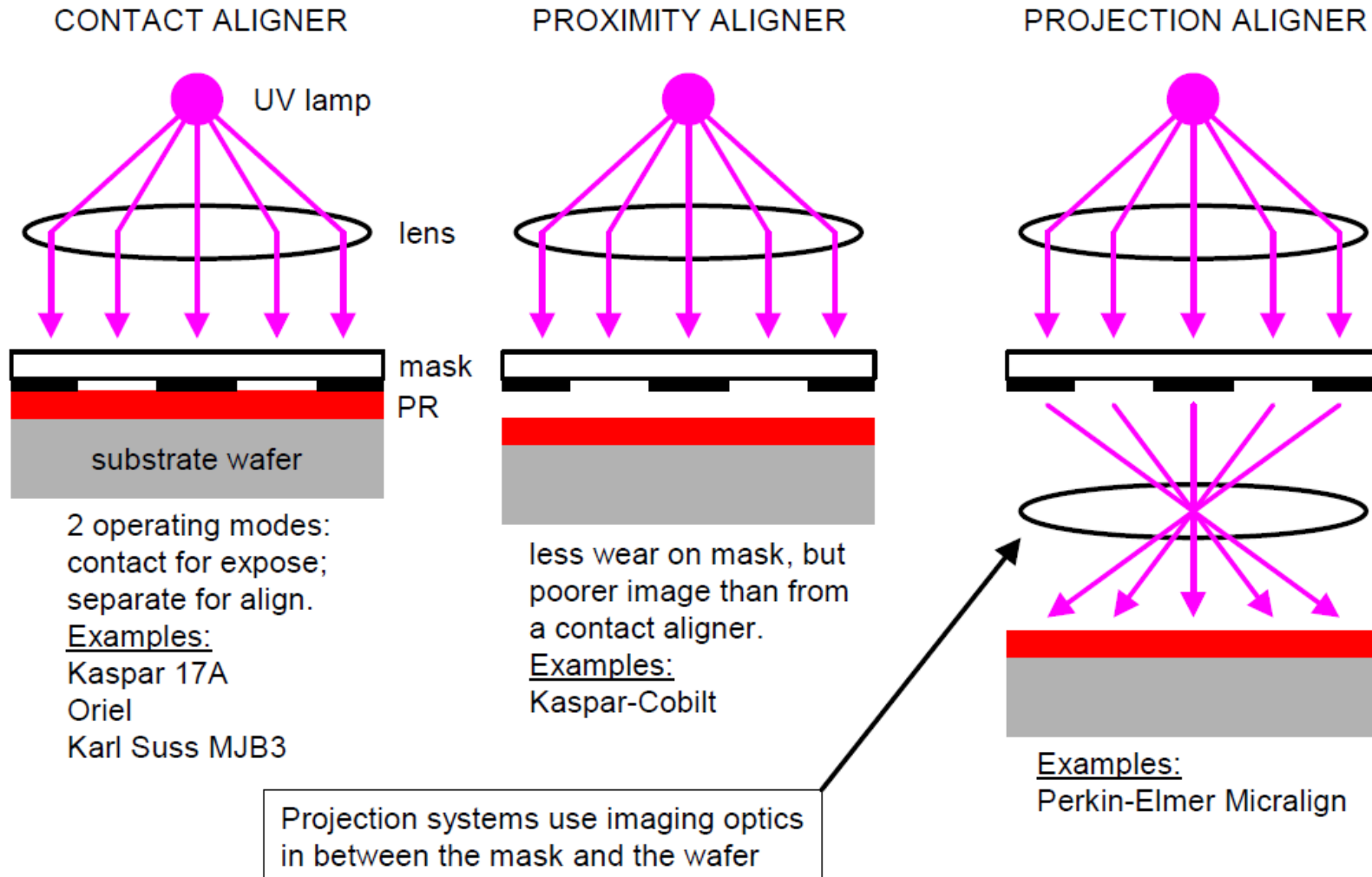
- Used to evaporate the coating solvent and to densify the resist after spin coating.
- Typical thermal cycles:
 - 90-100°C for 20 min. in a convection oven
 - 75-85°C for 45 sec. on a hot plate
- Commercially, microwave heating or IR lamps are also used in production lines.
- Hot plating the resist is usually faster, more controllable, and does not trap solvent like convection oven baking.



Overview of Align/Expose/Develop Steps



Alignment and Exposure Hardware



http://www.youtube.com/watch?v=9uJ09p_KG_U&feature=fvsr

Postbake (Hard Bake)

- Used to stabilize and harden the developed photoresist prior to processing steps that the resist will mask.
- Main parameter is the plastic flow or glass transition temperature.
- Postbake removes any remaining traces of the coating solvent or developer.
- This eliminates the solvent burst effects in vacuum processing.
- Postbake introduces some stress into the photoresist.
- Some shrinkage of the photoresist may occur.
- Longer or hotter postbake makes resist removal much more difficult.

<http://www.youtube.com/watch?v=9x3Lh1ZfggM>

<http://www.youtube.com/watch?v=63SPa0Lx9-c>

Photoresist Removal (Stripping)

- Want to remove the photoresist and any of its residues.
- Simple solvents are generally sufficient for non-postbaked photoresists:
 - Positive photoresists:
 - acetone
 - trichloroethylene (TCE)
 - phenol-based strippers (Indus-Ri-Chem J-100)
 - Negative photoresists:
 - methyl ethyl ketone (MEK), $\text{CH}_3\text{COC}_2\text{H}_5$
 - methyl isobutyl ketone (MIBK), $\text{CH}_3\text{COC}_4\text{H}_9$
- Plasma etching with O_2 (ashing) is also effective for removing organic polymer debris.

Basics of Photolithography for Processing

- Microfabrication processes:
 - Additive → deposition
 - Subtractive → etching
 - Modifying → doping, annealing, or curing
- Two primary techniques for patterning additive and subtractive processes:
 - Etch-back:
 - photoresist is applied ovetop of the layer to be patterned
 - unwanted material is etched away
 - Lift-off:
 - patterned layer is deposited over top of the photoresist
 - unwanted material is lifted off when resist is removed

Etch-back

1



deposit thin film of desired material

2



coat and pattern photoresist

3



etch film using photoresist as mask

4



remove photoresist

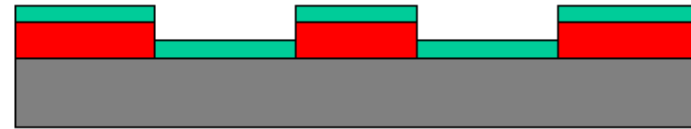
Lift-off

1



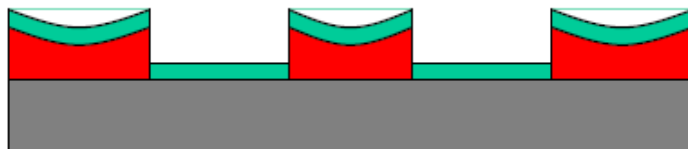
coat and pattern photoresist

2



deposit thin film of desired material

3



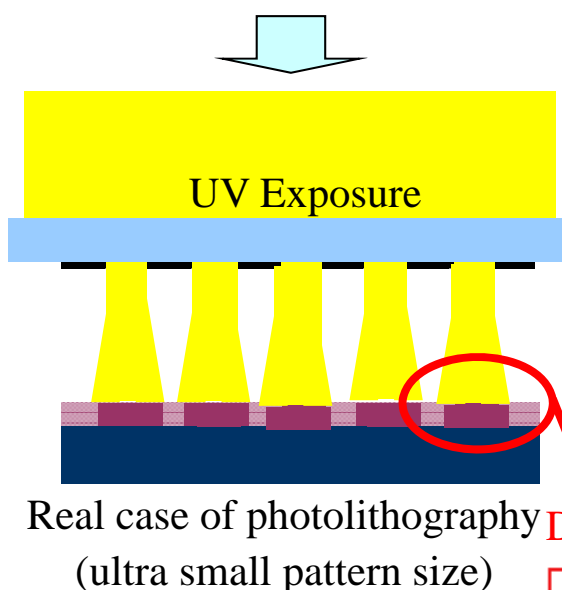
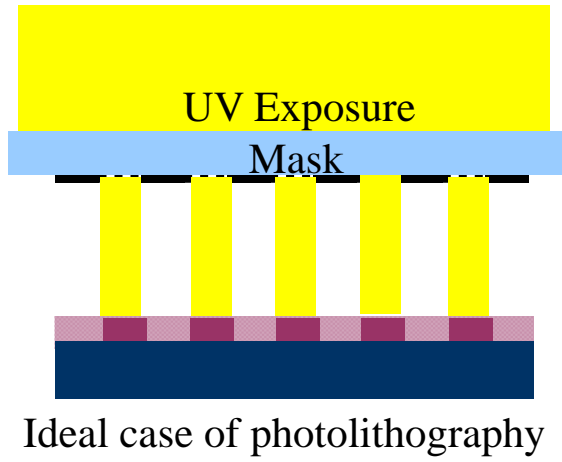
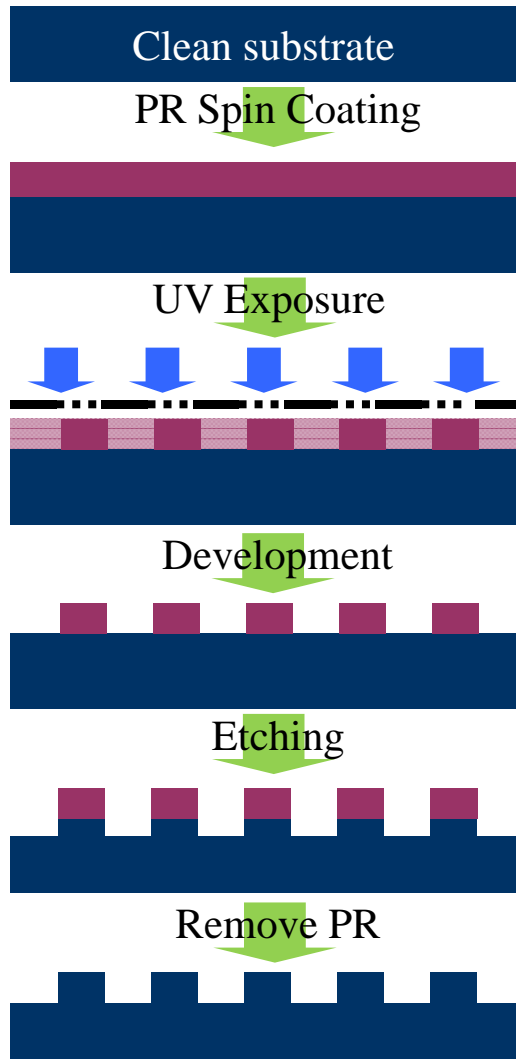
swell photoresist with a solvent

4



remove photoresist and thin film above it

Photolithography process and limitation



회절로 인해 같은 조건의 촬영 시 위와 같은 상이한 결과를 초래 (Image blur 현상 발생)

Diffraction effect

Limitation of Photolitho. In Display

- Increase of demands for nano/micro scale patterns with large pattern area
- Large-size substrate in digital display

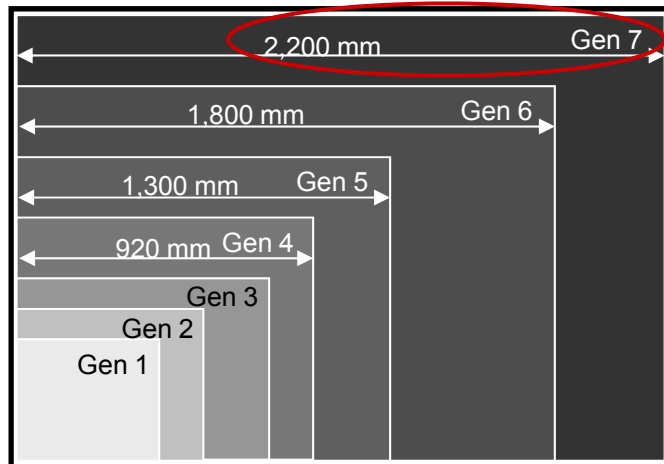
[100" LCD]



[Glass size 1950 X 2250mm]



[Glass substrate generation]



- Accomplishment of 7th generation display above 40"
→ Requirement for replication of large area pattern



- Limitation in conventional micro/nano technology
- Expensive lithography system for large area patterning
- Expensive process

Nano-replication



틀 준비

기름칠하기

반죽 붓기

구워주기

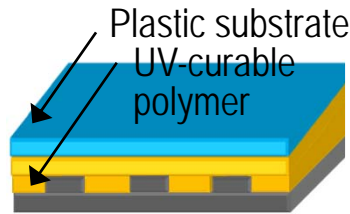
완성(떼어내기)



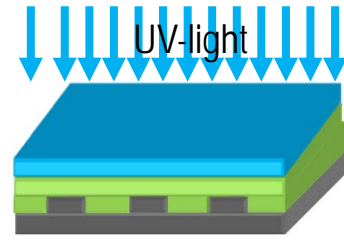
Mold preparation
(Photolitho. Etching,
Electroforming, etc)



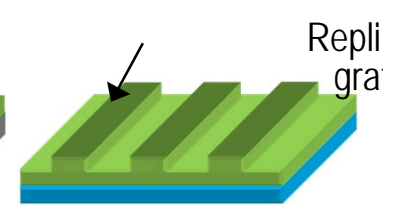
SAM Surface
treatment



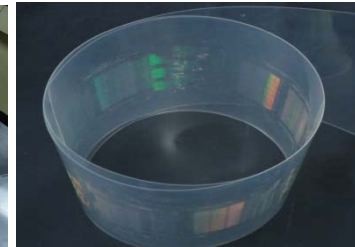
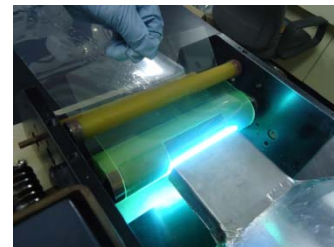
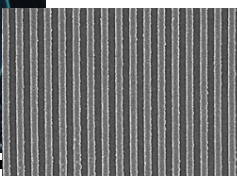
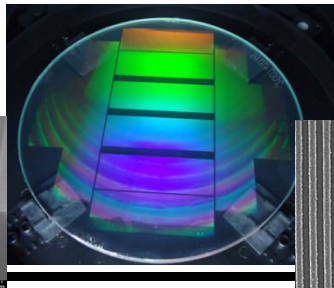
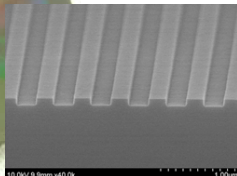
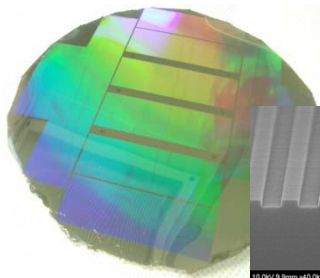
Material coating



Curing



Releasing

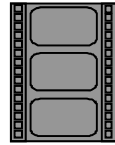
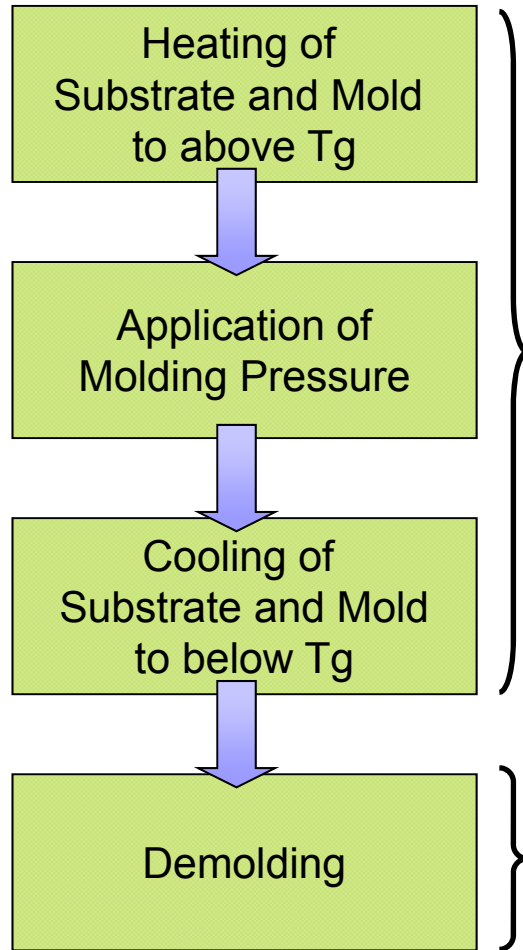


CAU

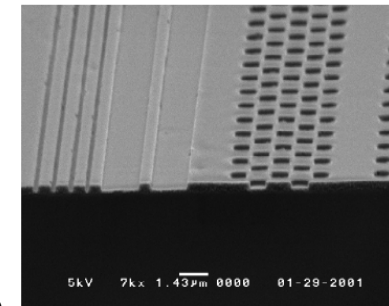
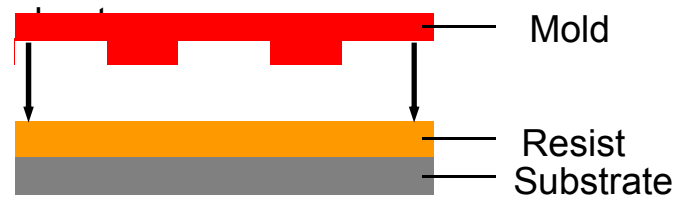
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Thermal nano-imprinting

- Procedures

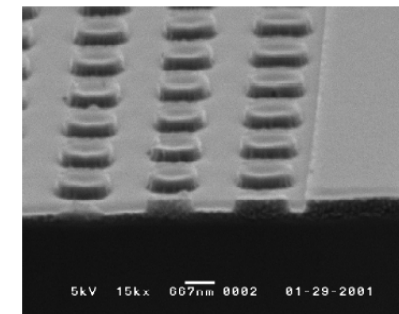
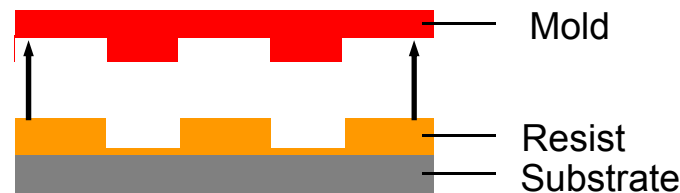


1. Press mold with



< Mold >

2. Remove mold



< Imprinted resist >

자료출처: <http://www.obducat.com/Default.aspx?ID=187>



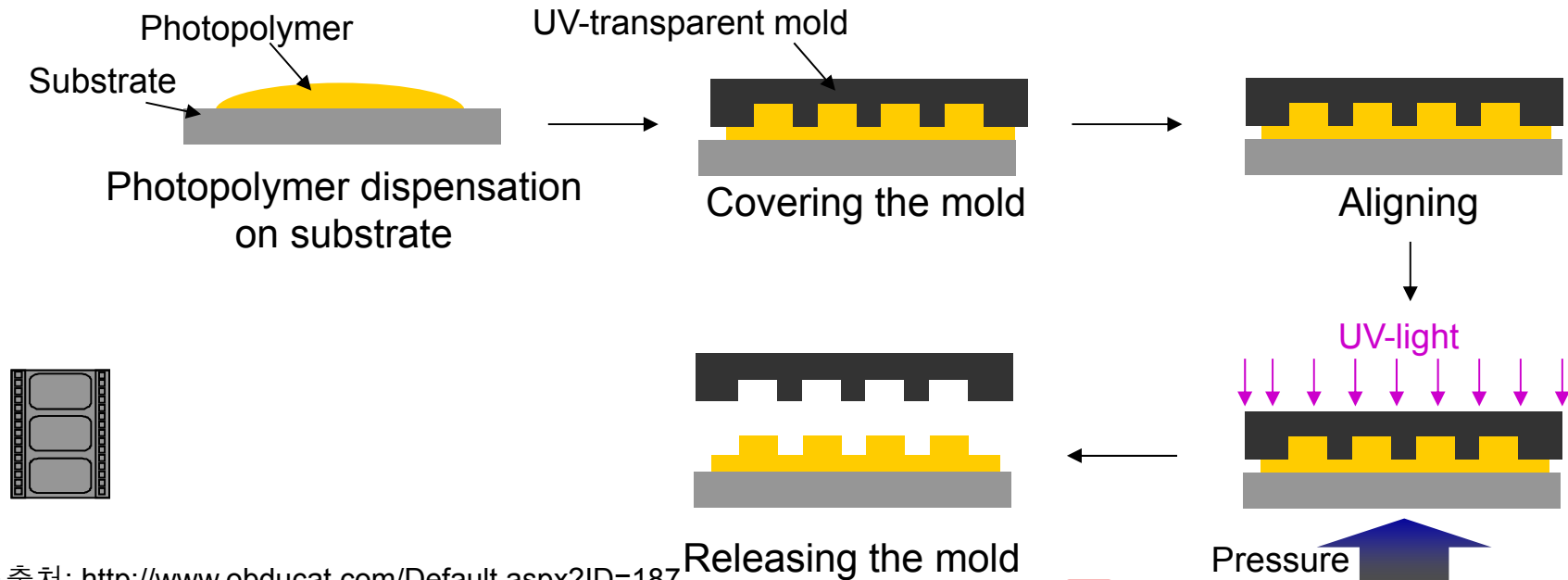
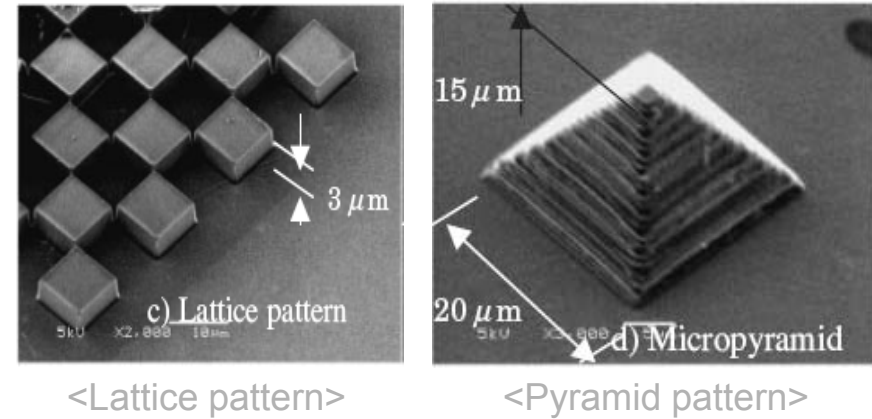
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UV nano-imprinting

■ UV nano-imprinting

- Material: UV-curable photopolymer
- Processing condition: room temp. & low pressure
- No fluidity problem

■ Procedures



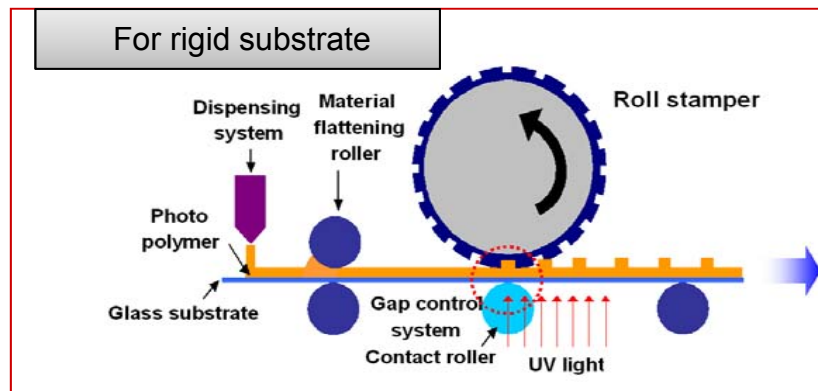
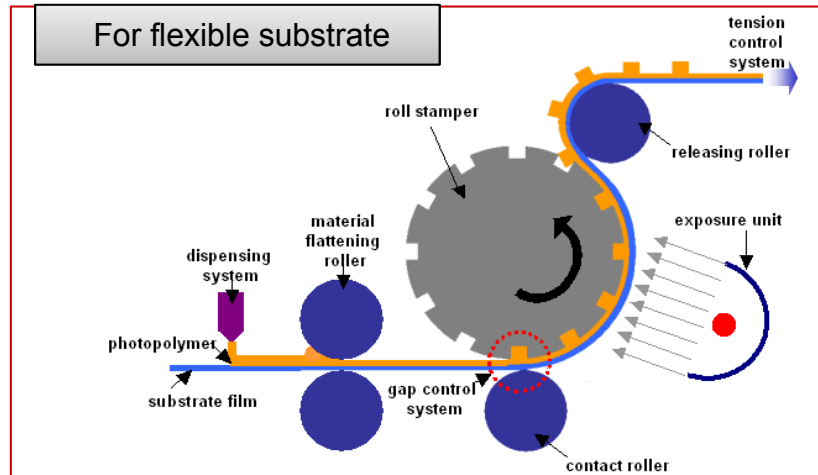
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JJAP, vol. 44, No. 7B, pp. 5600, 2005



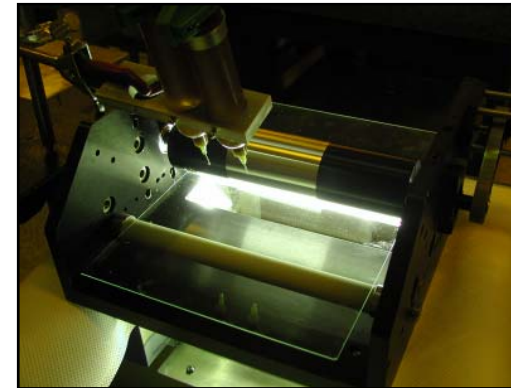
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Continuous UV nano-imprinting

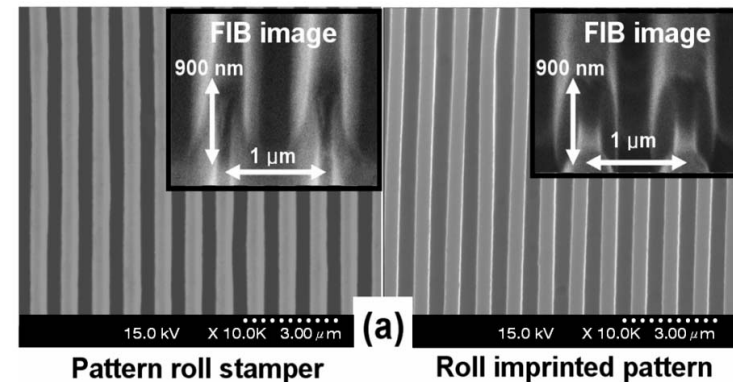
■ Design and construction of continuous UV nano imprinting system



■ Continuous UV nano-imprinting system



■ Fabrication results



1. Can replicate nano patterns of large area with high precision

2. Can replace conventional lithography process

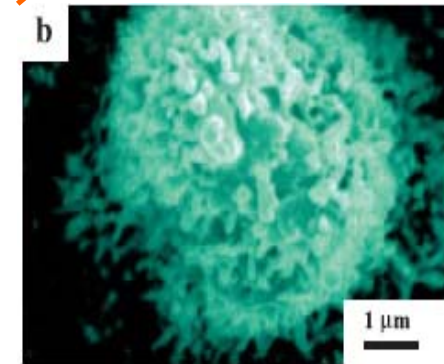
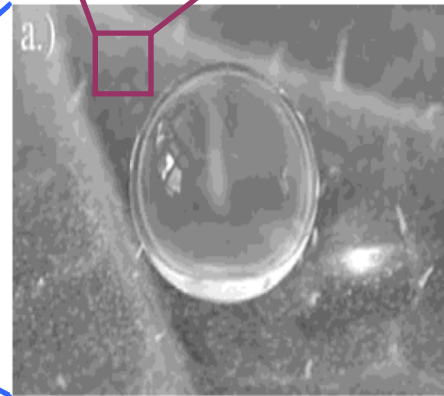
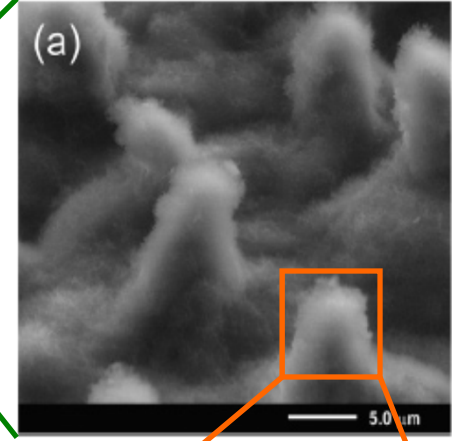
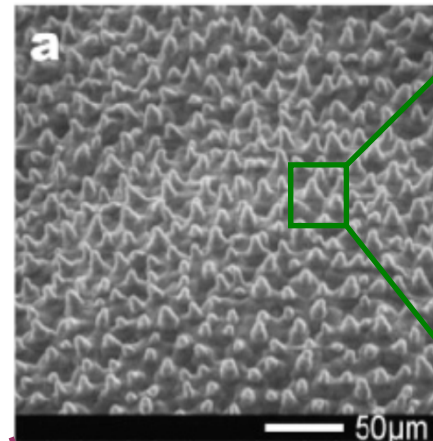
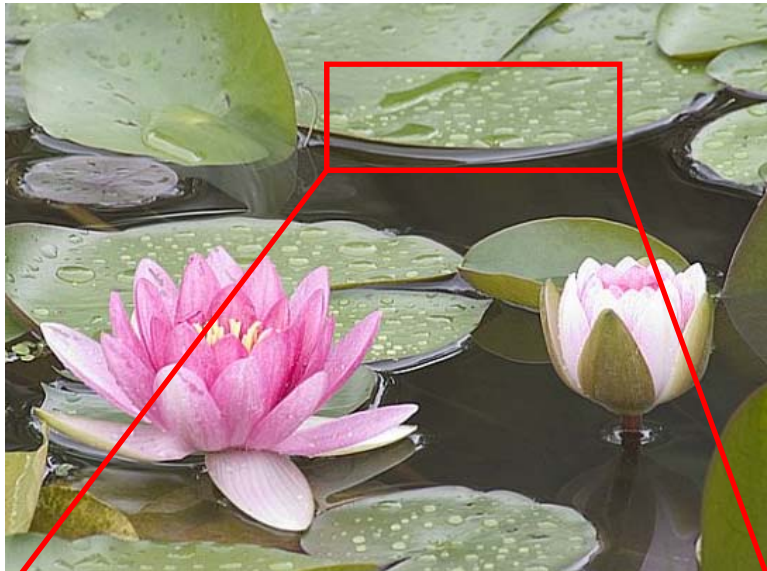


Nano-Imprinting 기술의 응용분야 1.

특수한 기능을 가진 자연물의 모사

물에 젖지 않는 자연물들 (1)

■ 연꽃 잎

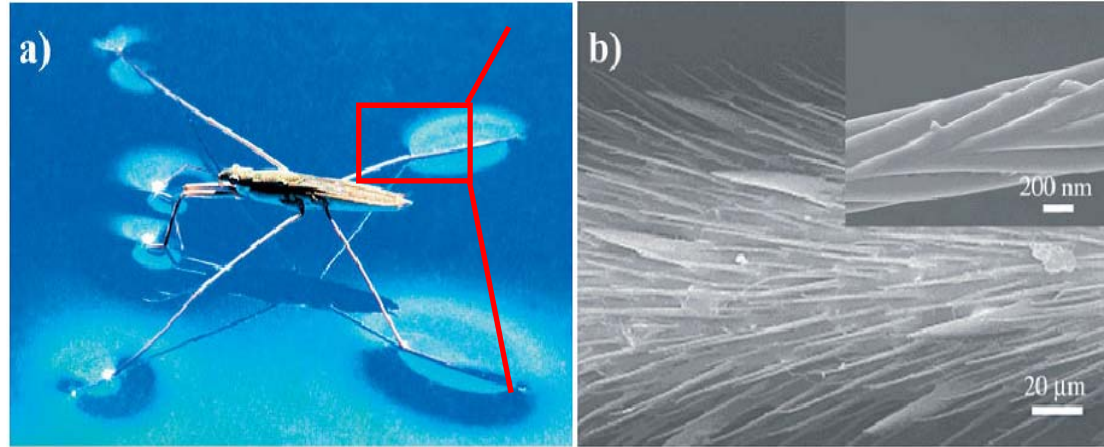


자료출처: <http://blog.empas.com/hl1vgt/>, Manhui Sun, Langmuir, Vol. 21, pp. 8979, 2004

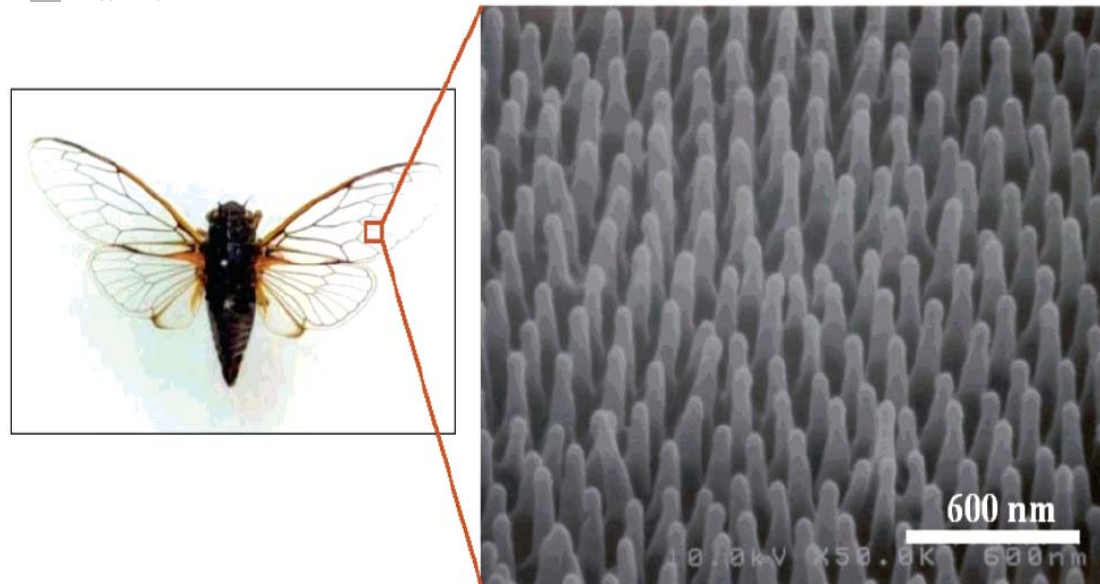
L. Feng, Advanced Material, Vol. 14, pp. 1857, 2002
Alexander Otten, Langmuir, Vol. 20, pp. 2405, 2004

물에 젖지 않는 자연물들 (2)

■ 소금쟁이



■ 매미



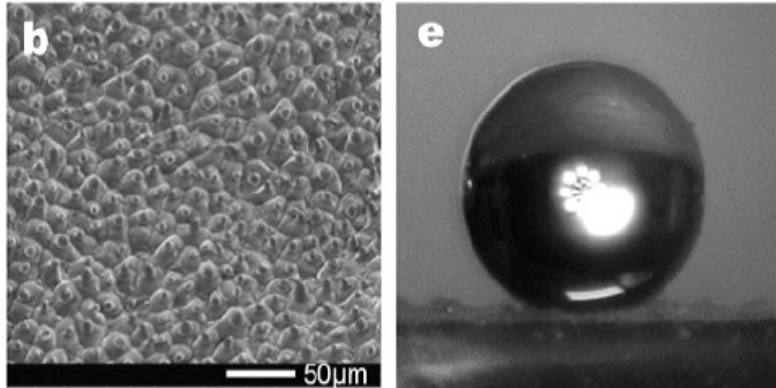
자료 출처: Woo Lee et al., Langmuir, Vol. 20, pp. 7665, 2004
Xuefeng Gao et al., Nature, Vol. 432, pp. 36, 2004



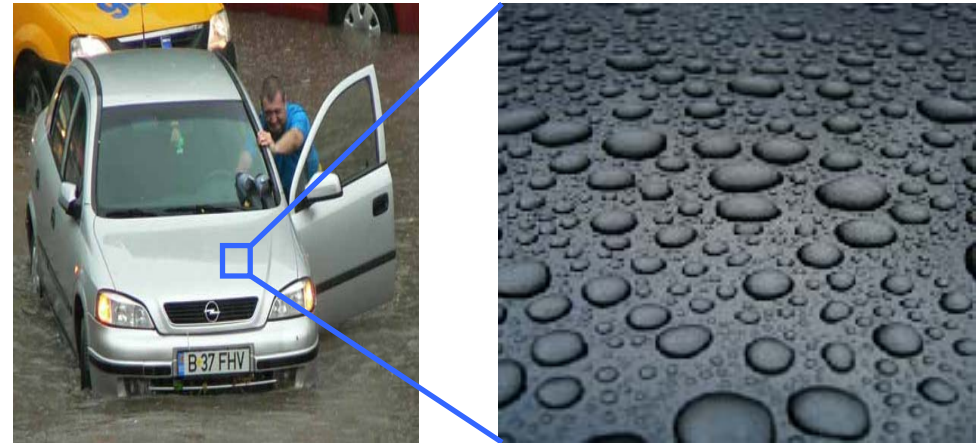
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물에 젖지 않는 표면의 제작

연꽃 잎의 모사

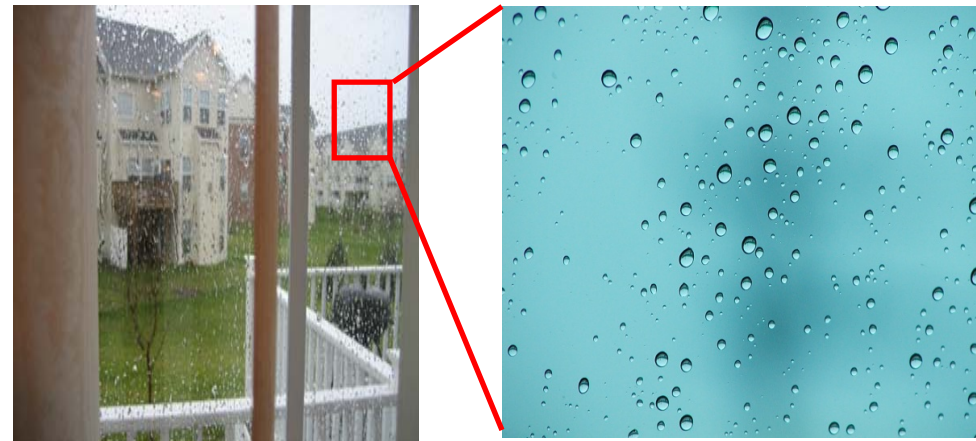
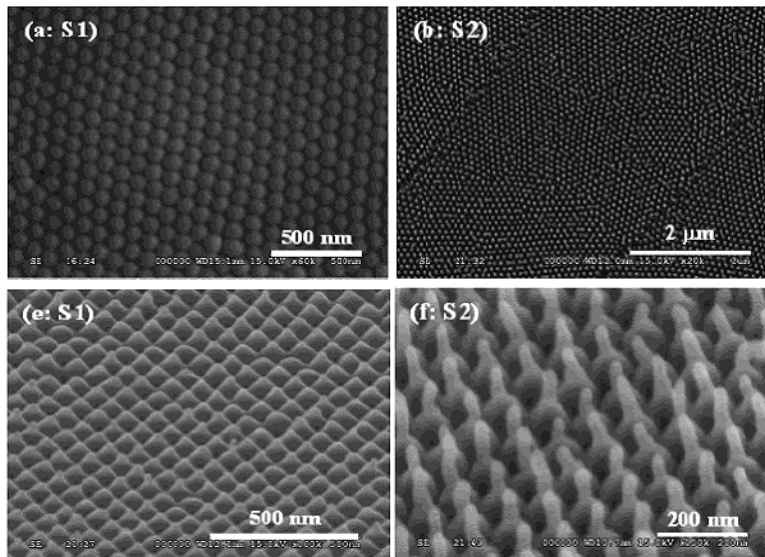


응용 분야



<자동차>

매미 날개의 모사



<유리창>

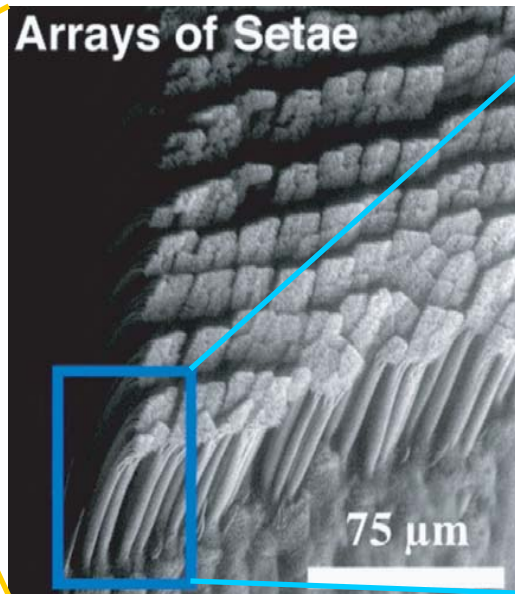
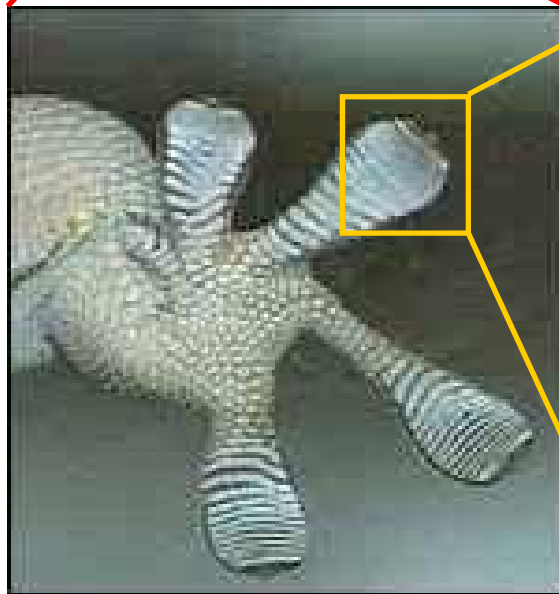
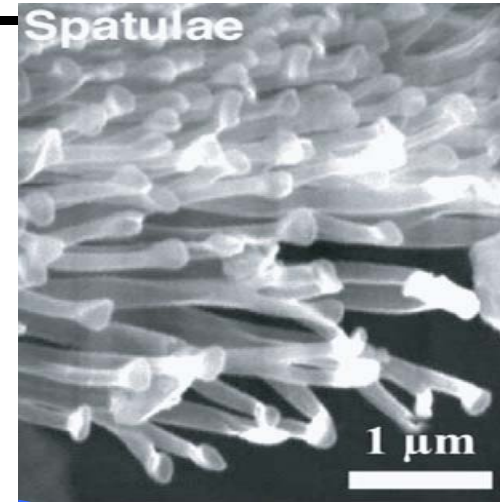
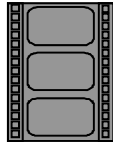
자료 출처: Manhui Sun et al., Langmuir, vol.21, pp.8978, 2005
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<http://www.dumitrup.com/blog/>



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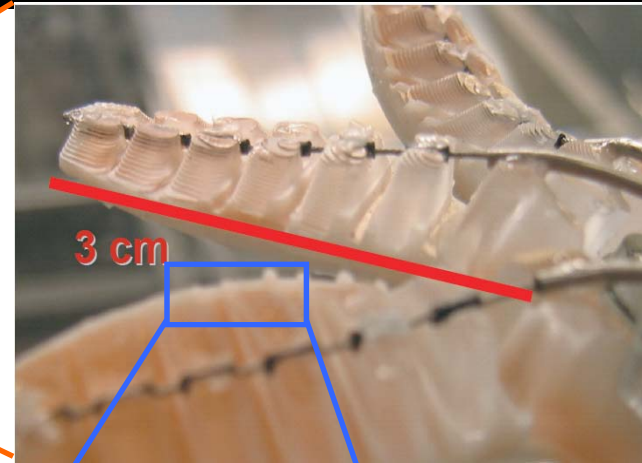
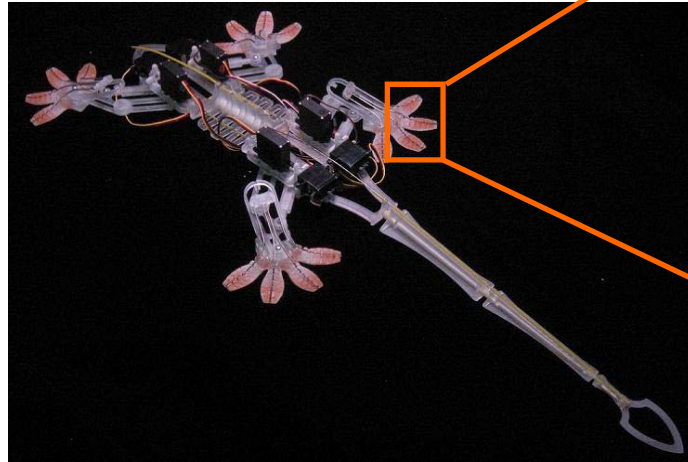
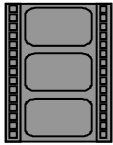
어떤 곳이든지 붙을 수 있는 발바닥

■ 게코 도마뱀의 발

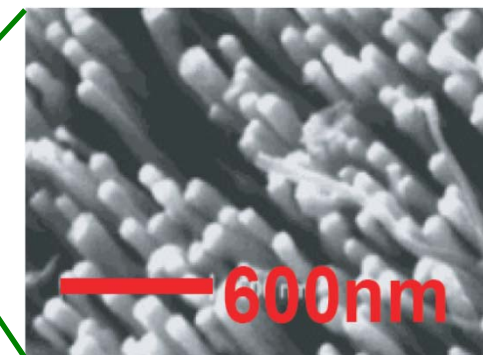
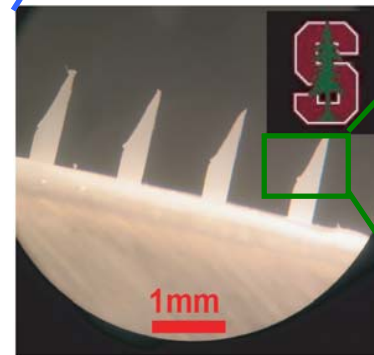


어떤 곳이든지 붙을 수 있는 표면의 제작

■ Stickybot

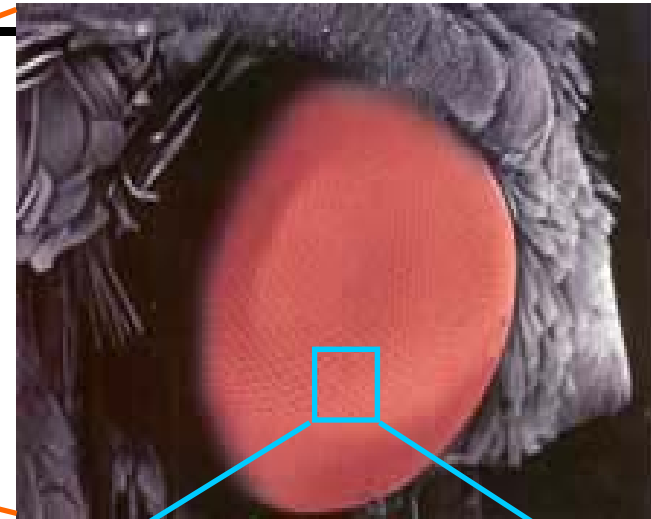


Vs.



빛이 반사하지 않는 표면

■ 나방의 눈



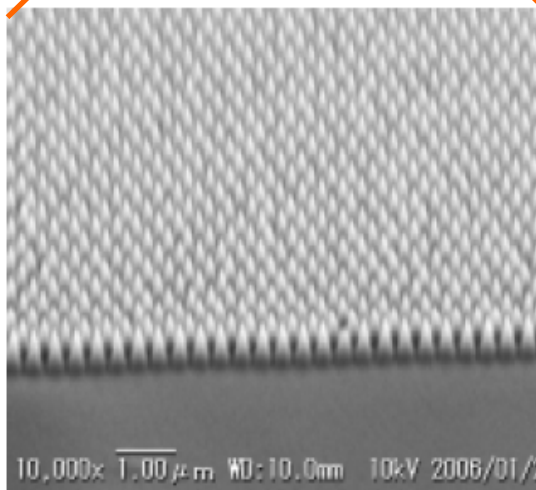
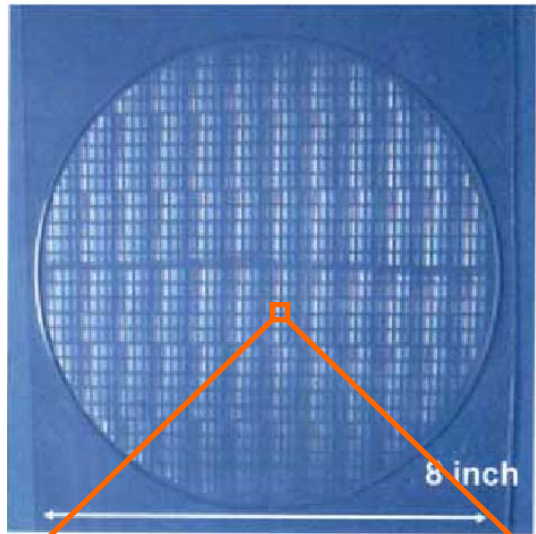
자료 출처: <http://www.motheye.com/>
<http://blog.empas.com/squirrel1226/>



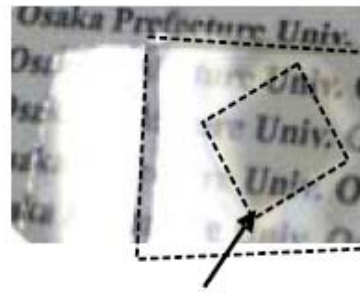
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빛이 반사하지 않는 표면의 제작

■ 나방 눈의 모사 패턴



■ 무반사면의 응용



Anti -reflective area
(5 mm square)

Before



With Motheye Anti-reflective film

Without Motheye

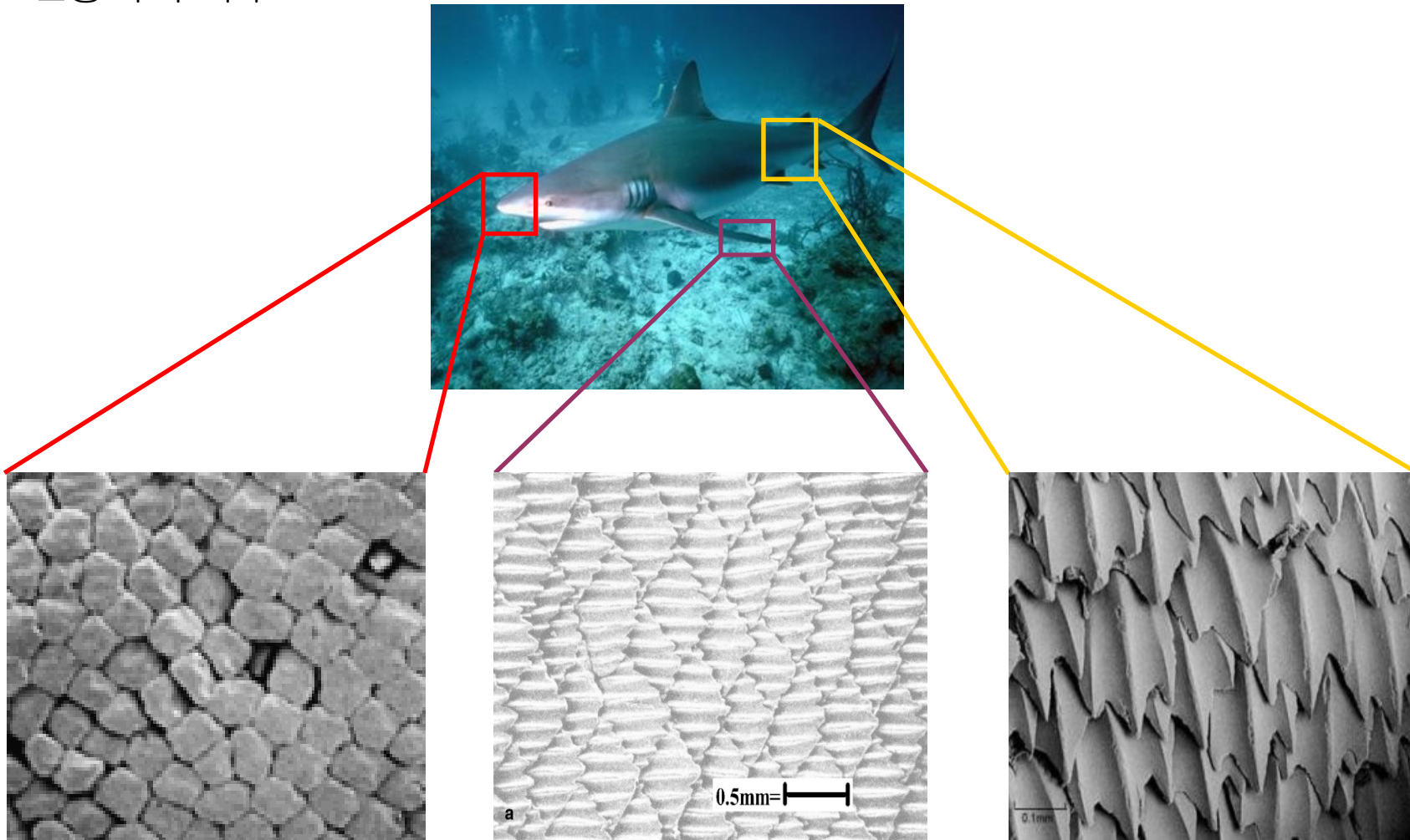


After Motheye



유체의 저항을 줄이는 표면

■ 상어의 피부

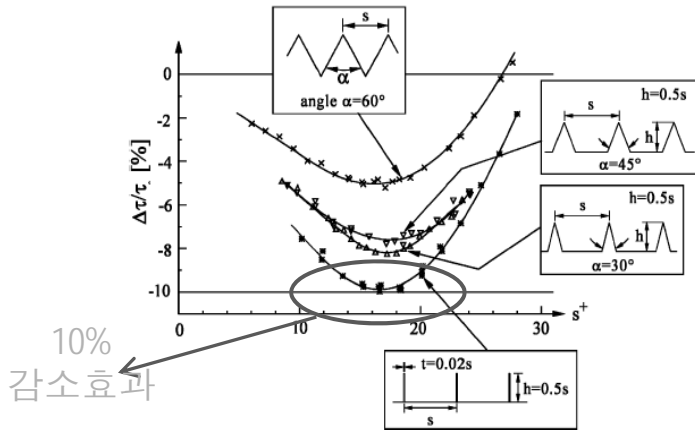
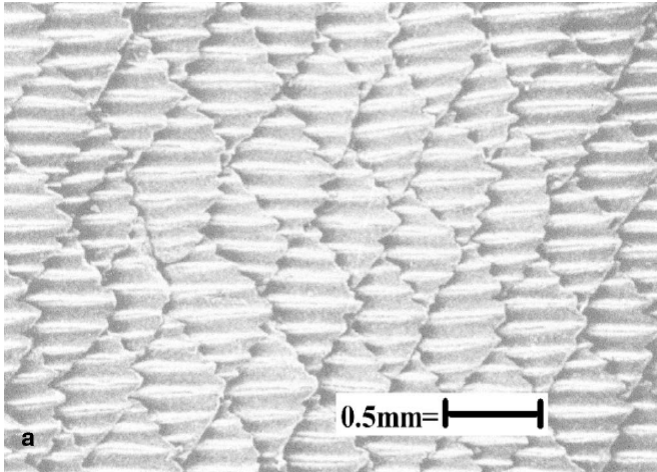


자료출처: <http://news.softpedia.com/news/The-Shark-Coating-42520.shtml>

D. W. Bechert, Naturwissenschaften, Vol. 87, pp.157, 2004

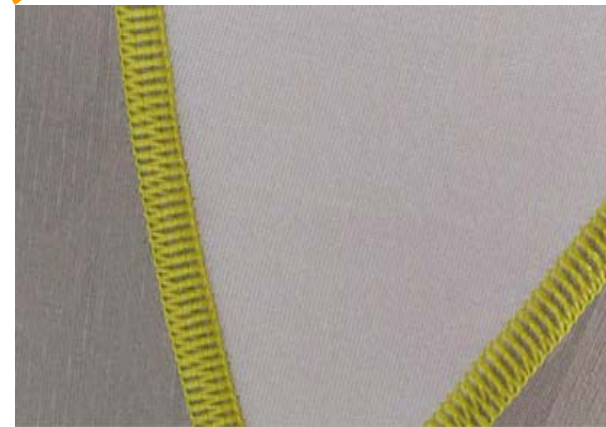
유체 저항을 줄이는 표면의 제작

■ 상어 피부



<Drag reduction of surface>

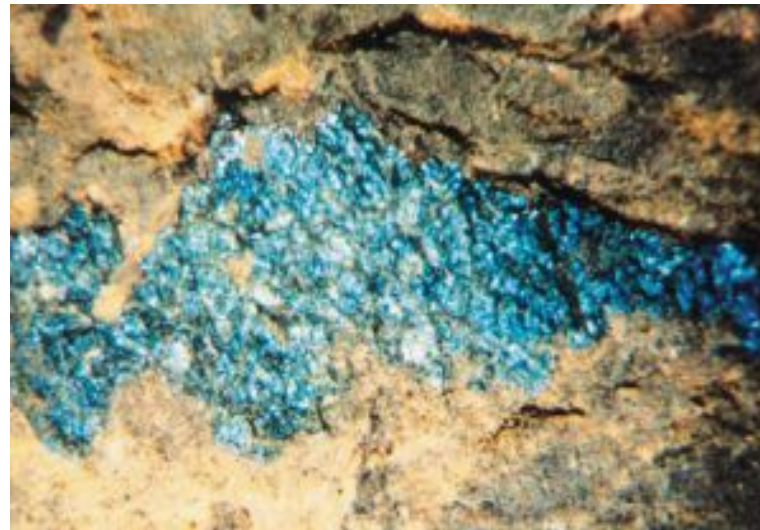
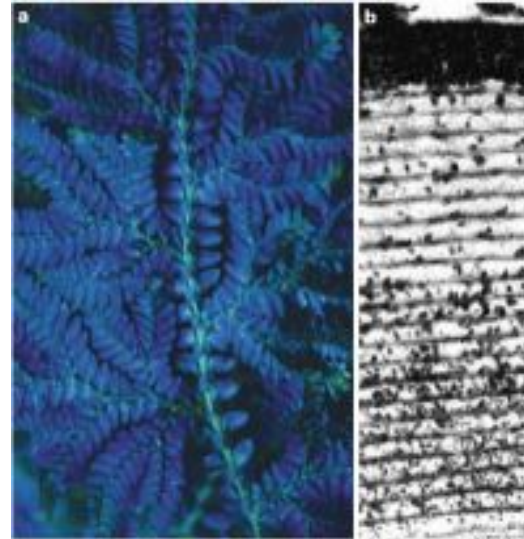
■ 상어 피부 형상의 응용 - 수영복



<Speed*speedo*> Fastskin II



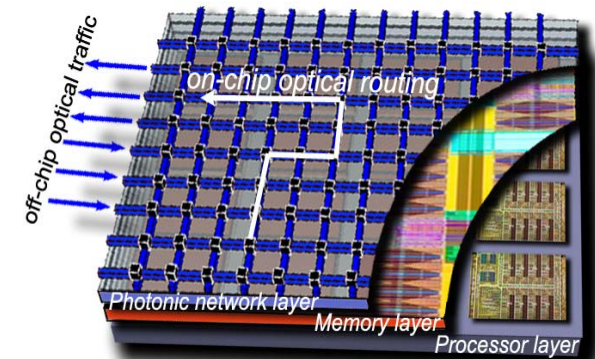
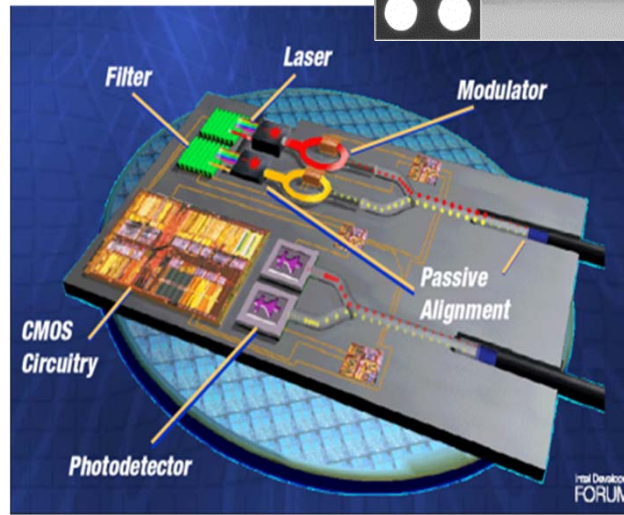
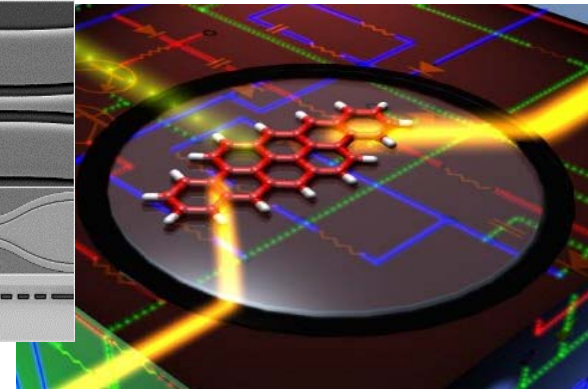
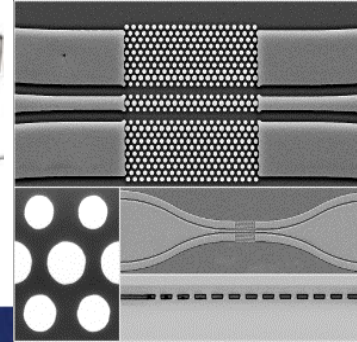
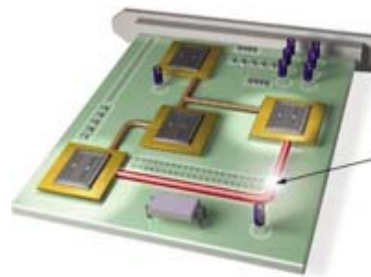
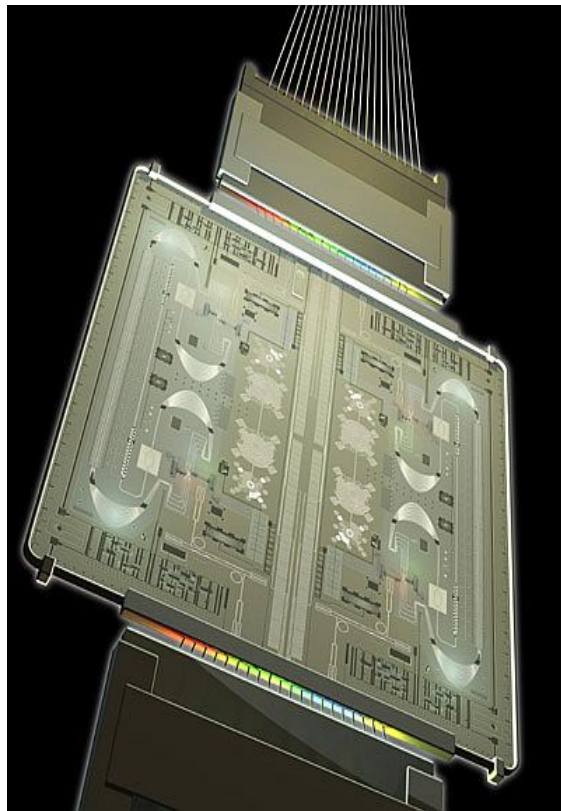
특정 파장의 빛을 반사하는 표면



Nano-Imprinting 기술의 응용분야 2.

Electronics

Photonic IC



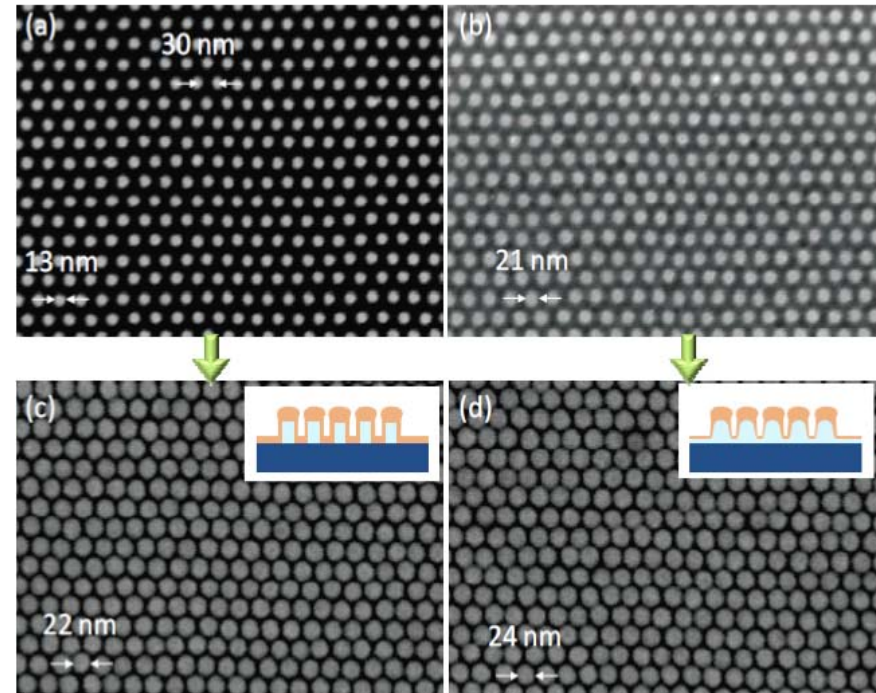
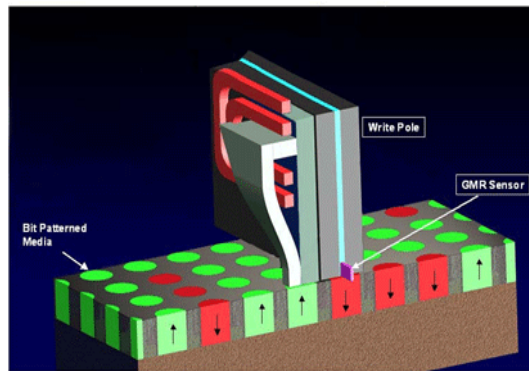
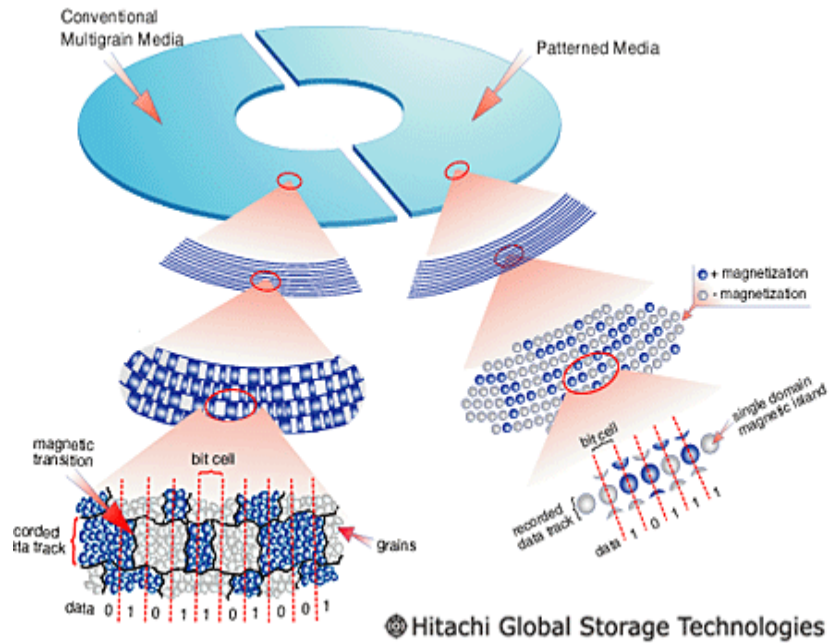
World's Fastest Optical Chip
wavelength division multiplexing (WDM)

Concept of photonic IC



Department of Mechanical Engineering
Chung-Ang University

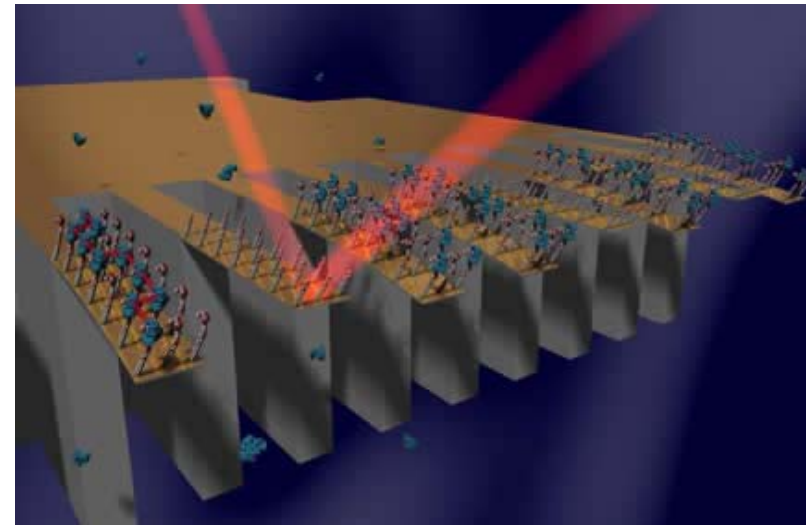
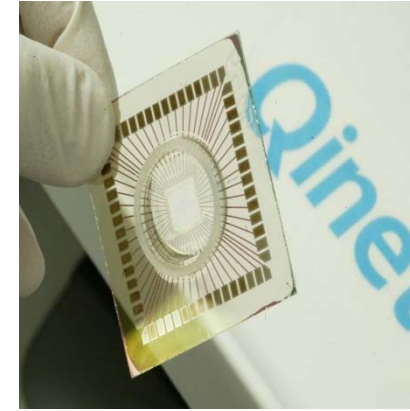
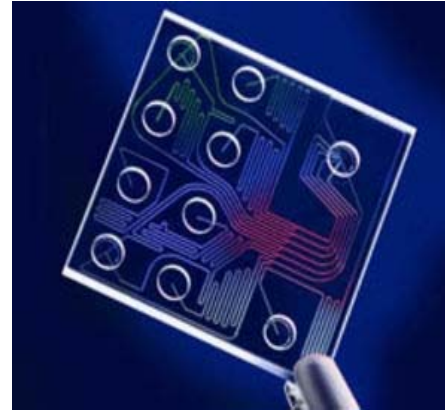
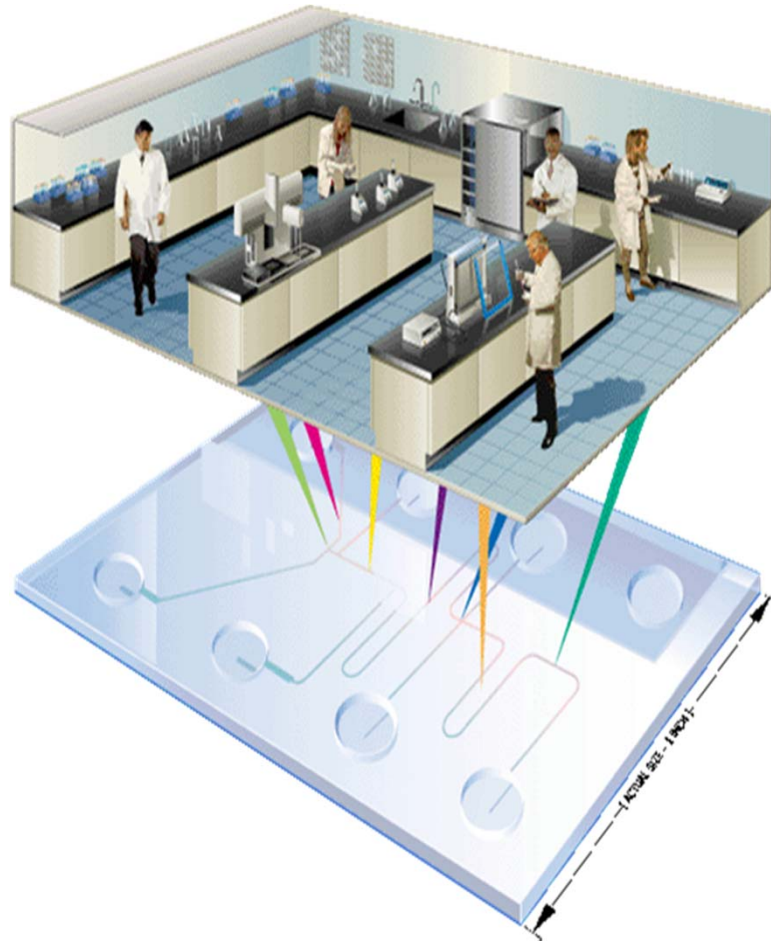
Patterned Media



Nano-Imprinting 기술의 응용분야 3.

Bio Application

Lab on a chip & Bio sensor



Micro-Cantilever biosensor

Scaffold tissue engineering

